

## SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

N-Channel Junction Silicon FET

# **25K3666**—Low-Frequency General-Purpose Amplifier, **Impedance Converter Applications**

#### **Applicatins**

· Low-frequency general-purpose amplifier, impedance conversion, infrared sensor applications.

#### **Features**

- · Small IGSS.
- Small Ciss

### **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

| Parameter                   | Symbol           | Conditions | Ratings     | Unit |
|-----------------------------|------------------|------------|-------------|------|
| Drain-to-Source Voltage     | V <sub>DSX</sub> |            | 30          | V    |
| Gate-to-Drain Voltage       | V <sub>GDS</sub> |            | -30         | V    |
| Gate Current                | IG               |            | 10          | mA   |
| Drain Current               | ID               |            | 10          | mA   |
| Allowable Power Dissipation | PD               |            | 200         | mW   |
| Junction Temperature        | Tj               |            | 150         | °C   |
| Storage Temperature         | Tstg             |            | -55 to +150 | °C   |

#### Electrical Characteristics at Ta=25°C

| Parameter                                  | Symbol   | Conditions  | Ratings |       |      | Unit  |
|--|----------|---|---------|-------|------|-------|
| Falanetei                                  |          |   | min     | typ   | max  | Offic |
| Gate-to-Drain Breakdown Voltage            | V(BR)GDS | I <sub>G</sub> =-10μA, V <sub>DS</sub> =0V        | -30     |       |      | V     |
| Gate-to-Source Leakage Current             | IGSS     | $V_{GS}$ =-20V, $V_{DS}$ =0V                      |         |       | -1.0 | nA    |
| Cutoff Voltage                             | VGS(off) | V <sub>DS</sub> =10V, I <sub>D</sub> =1μA         | -0.18   | -0.95 | -2.2 | V     |
| Drain Current                              | IDSS     | V <sub>DS</sub> =10V, V <sub>GS</sub> =0V         | 0.6*    |       | 6.0* | mA    |
| Forward Transfer Admittance                | yfs      | V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1kHz | 3.0     | 6.5   |      | mS    |
| Input Capacitance                          | Ciss     | V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1MHz |         | 4     |      | pF    |
| Reverse Transfer Capacitance               | Crss     | V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1MHz |         | 1.1   |      | pF    |
| Static Drain-to-Source On-State Resistance | RDS(on)  | VDS=10mV, VGS=0V                                  |         | 200   | ·    | Ω     |

#### \*: The 2SK3666 is classified by IDSS as follows: (unit: mA).

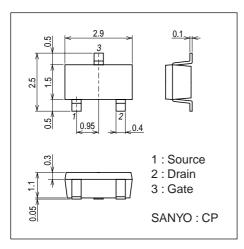
| Rank | 2          | 3          | 4          |  |
|------|------------|------------|------------|--|
| IDSS | 0.6 to 1.5 | 1.2 to 3.0 | 2.5 to 6.0 |  |

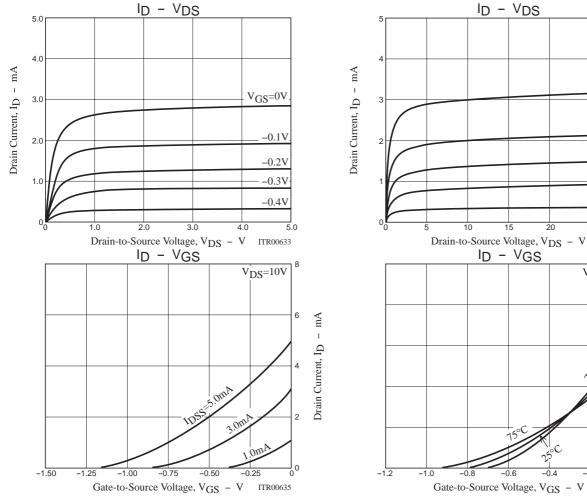
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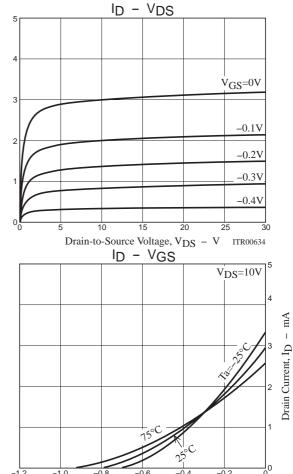
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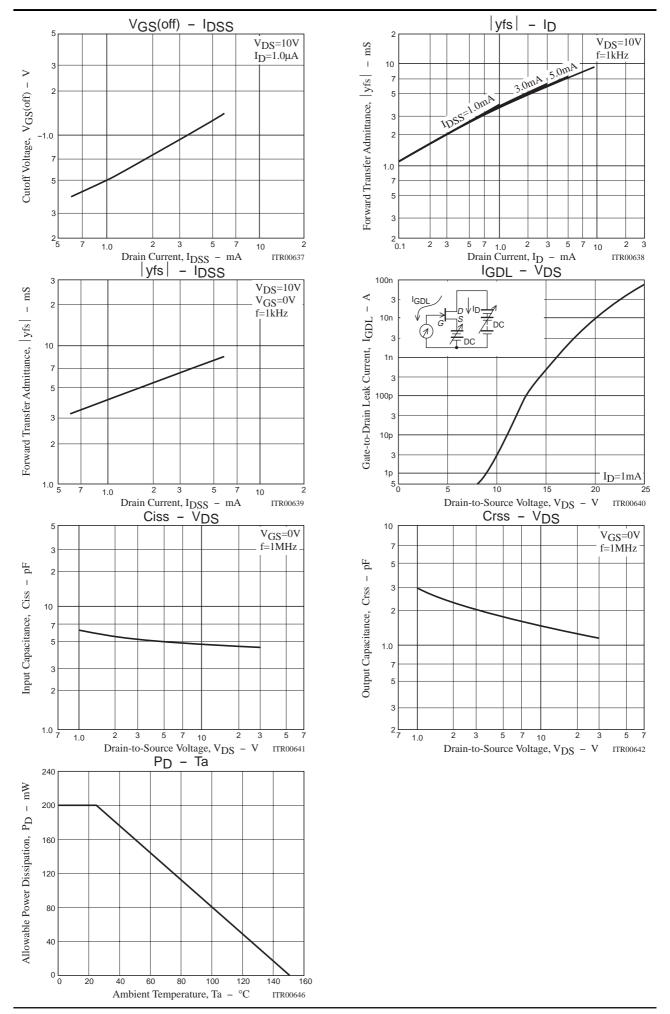
#### **Package Dimensions**

unit: mm 7013A-011









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